

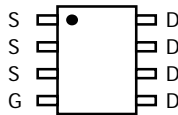
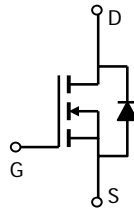
**AO4422A**
**N-Channel Enhancement Mode Field Effect Transistor**

**General Description**

The AO4422A uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for use as a load switch or in PWM applications. The source leads are separated to allow a Kelvin connection to the source, which may be used to bypass the source inductance. *Standard Product AO4422A is Pb-free (meets ROHS & Sony 259 specifications). AO4422AL is a Green Product ordering option. AO4422A and AO4422AL are electrically identical.*

**Features**

$V_{DS} (V) = 30V$   
 $I_D = 11A \quad (V_{GS} = 10V)$   
 $R_{DS(ON)} < 15m\Omega \quad (V_{GS} = 10V)$   
 $R_{DS(ON)} < 24m\Omega \quad (V_{GS} = 4.5V)$


**SOIC-8**

**Absolute Maximum Ratings  $T_A=25^\circ C$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>A</sup>	$I_D$	$T_A=25^\circ C$	11
		$T_A=70^\circ C$	9.3
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	50	A
Power Dissipation	$P_D$	$T_A=25^\circ C$	3
		$T_A=70^\circ C$	2.1
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ C$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	$t \leq 10s$	31	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A</sup>		Steady-State	59	$^\circ C/W$
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	16	24	$^\circ C/W$

Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$ , $V_{GS}=0\text{V}$	30			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=24\text{V}$ , $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$		0.003	1	$\mu\text{A}$
					5	
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 20\text{V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	1	1.7	3	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$ , $V_{DS}=5\text{V}$	30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$ , $I_D=11\text{A}$ $T_J=125^\circ\text{C}$		11.7	15	m $\Omega$
				18	22	
		$V_{GS}=4.5\text{V}$ , $I_D=9\text{A}$		18	24	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=5\text{V}$ , $I_D=11\text{A}$		19		S
$V_{SD}$	Diode Forward Voltage	$I_S=1\text{A}$ , $V_{GS}=0\text{V}$		0.76	1	V
$I_S$	Maximum Body-Diode Continuous Current				4.5	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}$ , $V_{DS}=15\text{V}$ , $f=1\text{MHz}$		955	1200	pF
$C_{oss}$	Output Capacitance			145		pF
$C_{riss}$	Reverse Transfer Capacitance			112		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}$ , $V_{DS}=0\text{V}$ , $f=1\text{MHz}$		0.5	0.85	$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$ , $V_{DS}=15\text{V}$ , $I_D=11\text{A}$		17	24	nC
$Q_g(4.5\text{V})$	Total Gate Charge			9	12	nC
$Q_{gs}$	Gate Source Charge			3.4		nC
$Q_{gd}$	Gate Drain Charge			4.7		nC
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=10\text{V}$ , $V_{DS}=15\text{V}$ , $R_L=1.35\Omega$ , $R_{GEN}=3\Omega$		5	6.5	ns
$t_r$	Turn-On Rise Time			6	7.5	ns
$t_{D(off)}$	Turn-Off Delay Time			19	25	ns
$t_f$	Turn-Off Fall Time			4.5	6	ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=11\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		19	21	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=11\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		9	12	nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any a given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D. The static characteristics in Figures 1 to 6 are obtained using 80  $\mu\text{s}$  pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

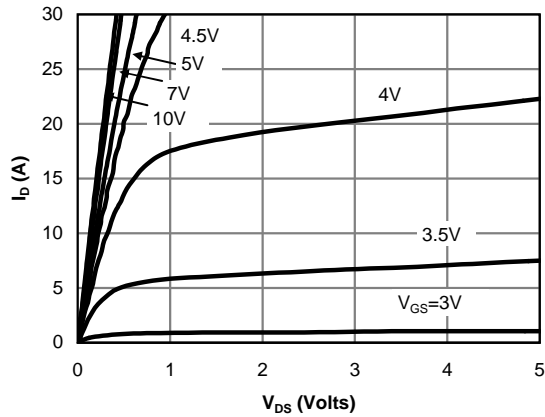


Fig 1: On-Region Characteristics

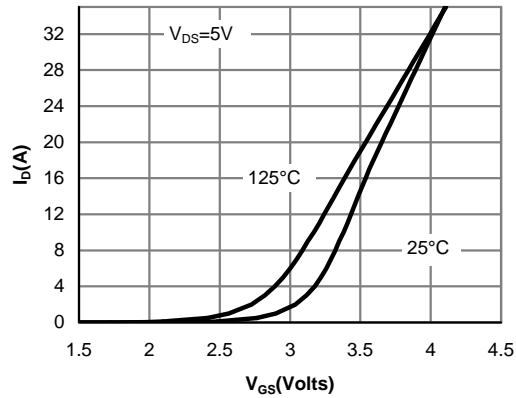


Figure 2: Transfer Characteristics

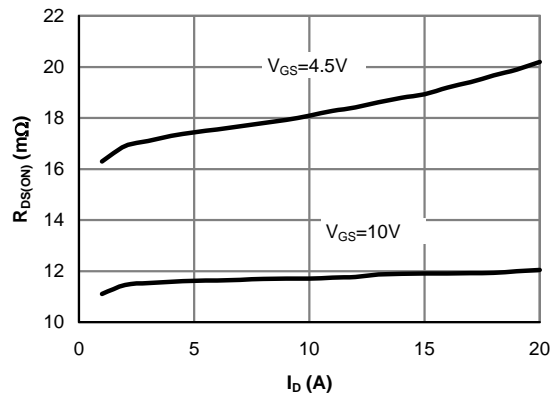


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

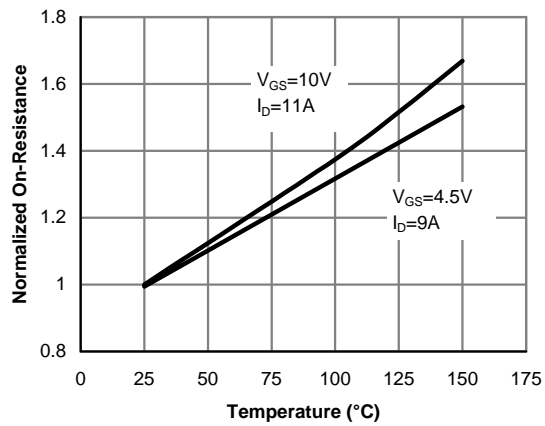


Figure 4: On-Resistance vs. Junction Temperature

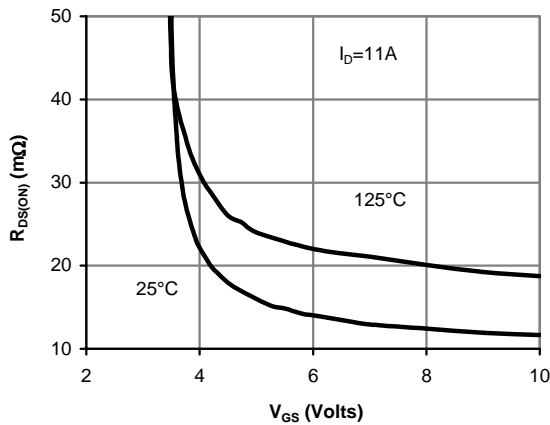


Figure 5: On-Resistance vs. Gate-Source Voltage

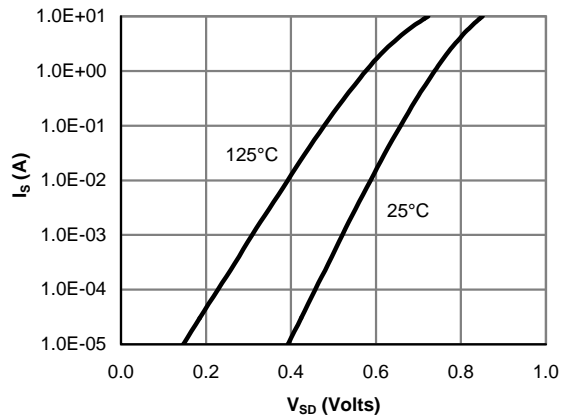


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

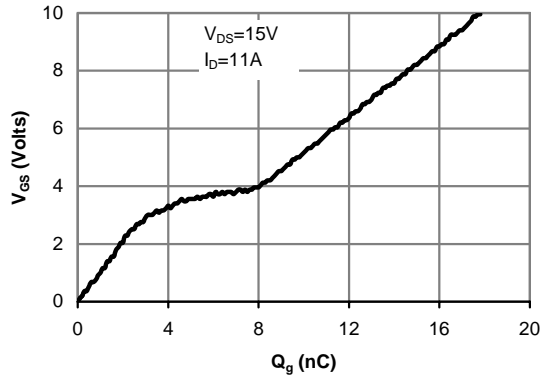


Figure 7: Gate-Charge Characteristics

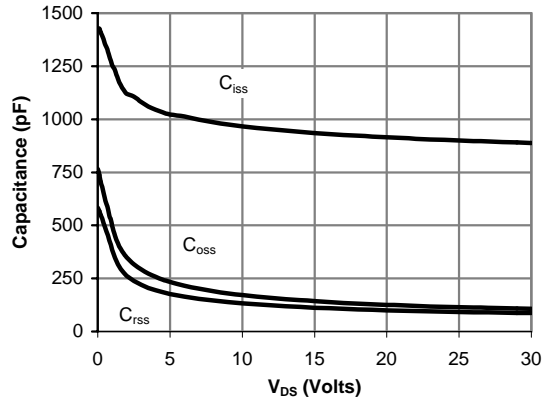


Figure 8: Capacitance Characteristics

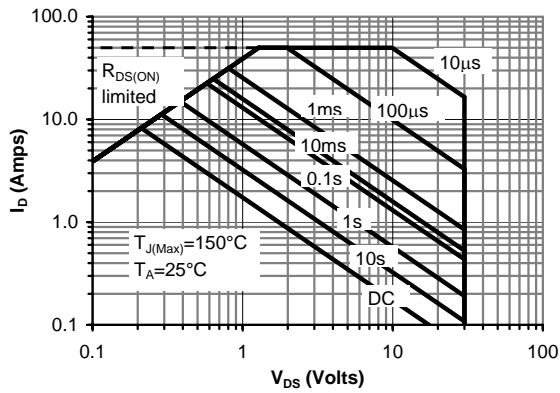


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

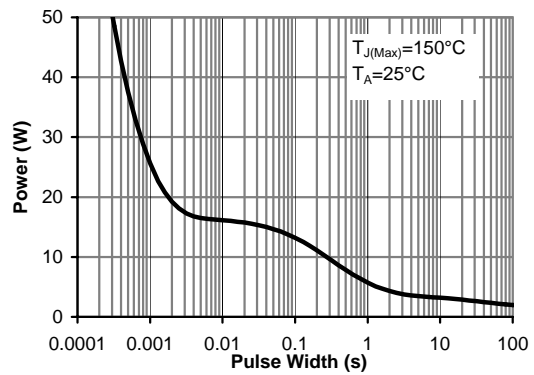


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

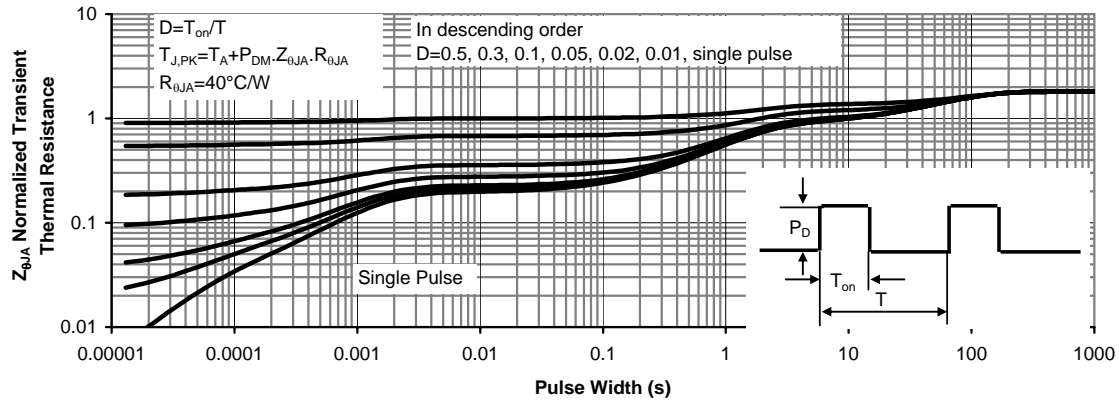


Figure 11: Normalized Maximum Transient Thermal Impedance